



Docket No.: M4065.0698/P698

Certificate

(PATENT)

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Letters Patent of: Kristy A. Campbell et al.

Patent No.: 6,881,623

Issued: April 19, 2005

MAY 1 8 2005 For: METHOD OF FORMING of Correction

CHALCOGENIDE COMPRISING DEVICES, METHOD OF FORMING A PROGRAMMABLE MEMORY CELL OF MEMORY CIRCUITRY, AND A

CHALCOGENIDE COMPRISING DEVICE

## REQUEST FOR CERTIFICATE OF CORRECTION PURSUANT TO 37 CFR 1.322

MS Post Issue Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

Upon reviewing the above-identified patent, Patentees noted typographical errors which should be corrected.

#### In OTHER PUBLICATIONS:

On the cover page, please correct the following:

"D.B. Johnson, et al., "Lateral Diffusion in Ag-Be Thin-Film Couples", Journal of Applied Physics, Vol. 40, No. 1, Jan. 1963, pp. 149-152" should read -- D.B. Johnson, et al., "Lateral Diffusion in Ag-Se Thin-Film Couples", Journal of Applied Physics, Vol. 40, No. 1, January 1969, pp. 149-152--.

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"U.S. Appl. No. 09/778,963, filed Feb. 8, 2001, Moore" should read --U.S. Appl. No. 09/779,983, filed Feb. 8, 2001, Moore--.

The following two items should be inserted:

--U.S. Appl. No. 10/077,867, filed Feb. 20, 2002, Campbell et al.--

--U.S. Appl. No. 10/232,757, filed Aug. 29, 2002, Li et al.--

On page 2, column 2, please correct the following:

"Hirose, et al., "High Memory Behavior and Reliability in Amorphous  $As_1S_0$  Film Doped with Ag", Jul. 17, 1980, pp. K187-K190" should read --Hirose, et al., "High Speed Memory Behavior and Reliability of an Amorphous  $As_2S_3$  Film Doped with Ag", Jul. 17, 1980, pp. K187-K190--.

"Hirose, et al., "Polarity-dependent memory switching and behavior of Ag dendrite in Ag-photodoped amorphous As<sub>1</sub>B<sub>1</sub> films", Journal of Applied Physics, vol. 47, No. 6, Jun. 1976, pp. 2787-2772" should read --Hirose, et al., "Polarity-dependent memory switching and behavior of Ag dendrite in Ag-photodoped amorphous As<sub>2</sub>S<sub>3</sub> films", Journal of applied Physics, Vol. 47, No. 6, Jun. 1976, pp. 2767-2772--.

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"Aron Technologies Corporation, Technology Description: *Programmable Metallization Cell (PMC)*, (pre-Jul. 7, 2000) pp. 1-5" should read --Axon Technologies Corporation, Technology Description: *Programmable Metallization Cell (PMC)*, (pre-Jul. 7, 2000) pp. 1-6--.

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The errors were not in the application as filed by applicants or in the IDS's filed (copies attached); accordingly no fee is required.

Patent No.: 6,881,623 Docket No.: M4065.0698/P698

Transmitted herewith is a proposed Certificate of Correction effecting such amendment. Patentees respectfully solicit the granting of the requested Certificate of Correction.

Dated: May 16, 2005

Respectfully submitted,

Thomas J. D'Amico

Registration No.: 28,371

Elizabeth Parsons

Registration No.: 52,499

DICKSTEIN SHAPIRO MORIN &

**OSHINSKY LLP** 

2101 L Street NW

Washington, DC 20037-1526

(202) 785-9700

Attorneys for Patentees

## UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

Page \_1\_ of \_3\_

PATENT NO.

6,881,623

APPLICATION NO. :

09/943,190

ISSUE DATE

April 19, 2005

INVENTOR(S)

Kristy A. Campbell et al.

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

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Page 2 of 3

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Approved for use through 04/30/2007. OMB 0651-0030 U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

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	AT		Mitkova, et al. "Dual	Chemical Role	of Ag as an Additive in Chalcogenide (	Glasses", Physical Review	v Letters, Vo.	. 83, No. 19, p	ps. 3848-3851.	

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ATTY. DOCKET NO. MI22-1668

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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary) MAY 1 6 2005

nsidered. Include copy of this form with next communication to applicant.

APPLICANT Kristy A. Campbell

GROUP

FILING DATE August 29, 2001 2818 U.S. PATENDENDEMENTS Document Date Name Class Subclass Initial Filing Date
If Appropriate ΑB AC AD ΑE AF AG AH ΑI ΑJ AK FOREIGN PATENT DOCUMENTS Document Number Date Country Translation No AL AM AN AO ΑP OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.) AR Mitkova, "Insulating and Semiconducting Glasses", Editor: P. Boolchand, World Scientific, New Jersey, 2000, pps. 813-843. AS Axon Technologies Corporation, TECHNOLOGY DESCRIPTION: Programmable Metallization Cell (PMC), (pre-July 7, 2000) pp. 1-6. ΑT Shimakawa et al., Photoinduced effects and metastability in amorphous semiconductors and insulators, 44 ADVANCES IN PHYSICS No. 6, 475-588 (Taylor & Francis Ltd. 1995) **KAMINER** DATE CONSIDERED XAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not

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APPLICANT: Kristy A. Campbell et al.

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August 29 2001

GROUP 2818

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